

# 7<sup>th</sup> IEEE Electron Devices Technology and Manufacturing (EDTM) Conference 2023

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21G. Emerging Devices Modeling I	
Session Date:	March 8(Wed.), 2023
Session Time:	15:15-16:25
Session Room:	Room G (#318)
Session Chair:	Prof. Dae Woong Kwon (Inha University)

[21G-1] [Invited] 15:15-15:40

#### DC and Transient Microscopic Simulation of Nanowire NMOSFETs

Christoph Jungemann<sup>1</sup>, Tobias Rippchen<sup>1</sup>, Maziar Noei<sup>2</sup> and Tobias Linn<sup>1</sup>

<sup>1</sup>RWTH Aachen University, <sup>2</sup>Infineon Technologies

[21G-2] 15:40-15:55

#### **Interpolative Device Models for Hafnia-Based FeFETs**

Imtiaz Hossen<sup>1</sup>, Andreu L. Glasmann<sup>2</sup>, Sina Najmaei<sup>2</sup> and Gina C. Adam<sup>1</sup>

<sup>1</sup>The George Washington University, <sup>2</sup>DEVCOM Army Research Laboratory

[21G-3] 15:55-16:10

### New Understanding of Screen Radius and Re-Evaluation of Memory Window in Cylindrical Ferroelectric Capacitor for High-Density 1T1C FeRAM

Minyue Deng<sup>1</sup>, Chang Su<sup>1</sup>, Zhiyuan Fu<sup>1</sup>, Kaifeng Wang<sup>1</sup>, Ru Huang<sup>1,2</sup> and Qianqian Huang<sup>1,2,3</sup>

<sup>1</sup>Peking University, <sup>2</sup>Beijing Advanced Innovation Center for Integrated Circuits, <sup>3</sup>Beijing

Superstring Academy of Memory Technology

[21G-4] 16:10-16:25

## Impact of Device Geometry, Physical Doping and Electrostatic Doping on the Frequency CV-Dispersion of TFT Devices with IWO Channels

Andrea Palmieri<sup>1</sup>, Karim Cherkaoui<sup>2</sup>, Khandker Akif Aabrar<sup>3</sup>, Yaoqiao Hu<sup>3</sup>, Luca Larcher<sup>1</sup>, Kyeongjae Cho<sup>4</sup>, Suman Datta<sup>3</sup>, Paul Hurley<sup>2</sup> and Milan Pešić<sup>1</sup>

<sup>1</sup>Applied Materials, <sup>2</sup>Tyndall National Institute, <sup>3</sup>Georgia Institute of Technology, <sup>4</sup>The University of Texas at Dallas